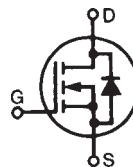


PolarHT™ Power MOSFET

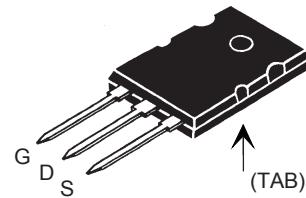
IXTK 102N30P

V_{DSS} = 300 V
I_{D25} = 102 A
R_{DS(on)} ≤ 33 mΩ

N-Channel Enhancement Mode
Avalanche Rated



Symbol	Test Conditions	Maximum Ratings		TO-264 (IXTK)
V_{DSS}	T _J = 25°C to 150°C	300	V	
V_{DGR}	T _J = 25°C to 150°C; R _{GS} = 1 MΩ	300	V	
V_{GSS}	Continuous	±20	V	
V_{GSM}	Transient	±30	V	
I_{D25}	T _C = 25°C	102	A	
I_{D(RMS)}	External lead current limit	75	A	
I_{DM}	T _C = 25°C, pulse width limited by T _{JM}	250	A	
I_{AR}	T _C = 25°C	60	A	
E_{AR}	T _C = 25°C	60	mJ	
E_{AS}	T _C = 25°C	2.5	J	
dv/dt	I _S ≤ I _{DM} , di/dt ≤ 100 A/μs, V _{DD} ≤ V _{DSS} , T _J ≤ 150°C, R _G = 4 Ω	10	V/ns	
P_D	T _C = 25°C	700	W	
T_J		-55 ... +150	°C	
T_{JM}		150	°C	
T_{stg}		-55 ... +150	°C	
T_L	1.6 mm (0.062 in.) from case for 10 s	300	°C	
T_{SOLD}	Plastic body for 10 s	260	°C	
M_d	Mounting torque	1.13/10	Nm/lb.in.	
Weight	TO-264	10	g	



G = Gate D = Drain
S = Source TAB = Drain

Features

- International standard package
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
 - easy to drive and to protect

Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions (T _J = 25°C, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	V _{GS} = 0 V, I _D = 250 μA	300		V
V_{GS(th)}	V _{DS} = V _{GS} , I _D = 500 μA	2.5		5.0 V
I_{GSS}	V _{GS} = ±20 V _{DC} , V _{DS} = 0		±200	nA
I_{DSS}	V _{DS} = V _{DSS} V _{GS} = 0 V		25 250	μA
R_{DS(on)}	V _{GS} = 10 V, I _D = 0.5 I _{D25} Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %		33	mΩ

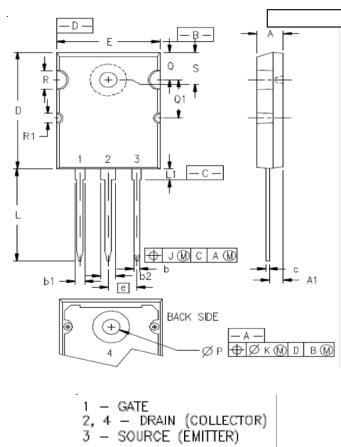
Symbol	Test Conditions	Characteristic Values		
		($T_j = 25^\circ C$, unless otherwise specified)	Min.	Typ.
g_{fs}	$V_{DS} = 10 V; I_D = 0.5 I_{D25}$, pulse test	45	57	S
C_{iss} C_{oss} C_{rss}	$V_{GS} = 0 V, V_{DS} = 25 V, f = 1 \text{ MHz}$	7500		pF
		1150		pF
		230		pF
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	$V_{GS} = 10 V, V_{DS} = 0.5 V_{DSS}, I_D = 60 A$ $R_G = 3.3 \Omega$ (External)	30		ns
		28		ns
		130		ns
		30		ns
$Q_{g(on)}$ Q_{gs} Q_{gd}	$V_{GS} = 10 V, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$	224		nC
		50		nC
		110		nC
R_{thJC}			0.18	$^\circ C/W$
R_{thCS}		0.15		$^\circ C/W$

Source-Drain Diode

Characteristic Values

Symbol	Test Conditions	Characteristic Values		
		($T_j = 25^\circ C$, unless otherwise specified)	Min.	Typ.
I_s	$V_{GS} = 0 V$		102	A
I_{sm}	Repetitive		250	A
V_{SD}	$I_F = I_s, V_{GS} = 0 V$, Pulse test, $t \leq 300 \mu s$, duty cycle $d \leq 2 \%$		1.5	V
t_{rr} Q_{RM}	$I_F = 25 A, -di/dt = 100 A/\mu s$ $V_R = 100 V, V_{GS} = 0 V$	250		ns
		3.3		μC

TO-264 (IXTK) Outline

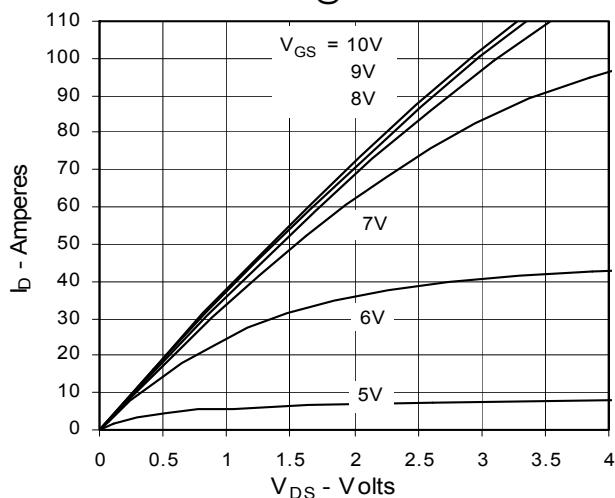


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b1	.087	.102	2.21	2.59
b2	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.799	19.30	20.29
e	.215 BSC		5.46 BSC	
J	.000	.010	0.00	0.25
K	.000	.010	0.00	0.25
L	.779	.842	19.79	21.39
L1	.087	.102	2.21	2.59
P	.122	.138	3.10	3.51
Q	.240	.256	6.10	6.50
Q1	.330	.346	8.38	8.79
R	.155	.187	3.94	4.75
R1	.085	.093	2.16	2.36
S	.243	.253	6.17	6.43

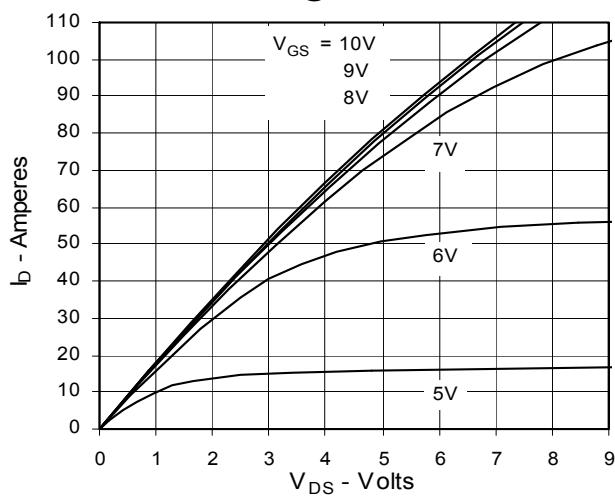
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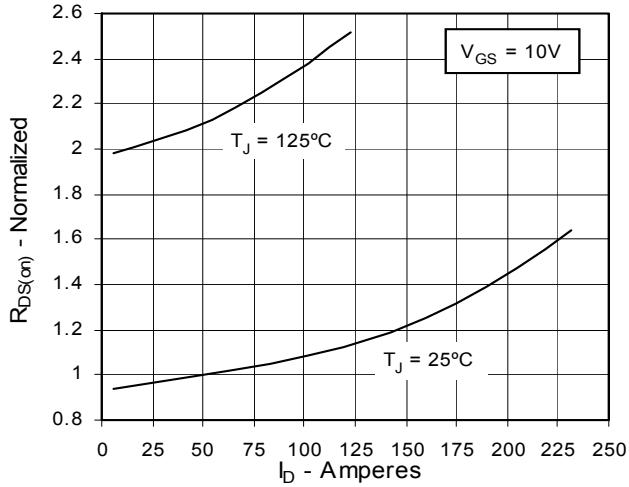
**Fig. 1. Output Characteristics
@ 25°C**



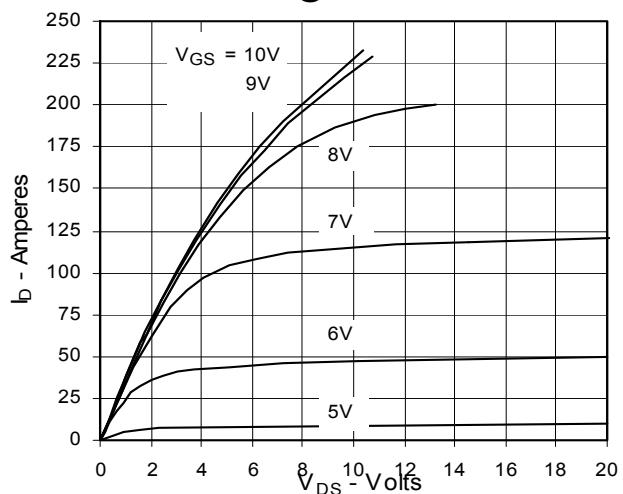
**Fig. 3. Output Characteristics
@ 125°C**



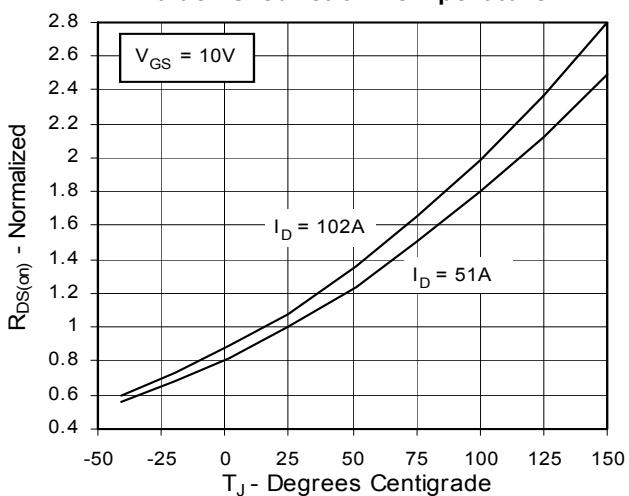
**Fig. 5. $R_{DS(on)}$ Normalized to
0.5 I_{D25} Value vs. I_D**



**Fig. 2. Extended Output Characteristics
@ 25°C**



**Fig. 4. $R_{DS(on)}$ Normalized to 0.5 I_{D25}
Value vs. Junction Temperature**



**Fig. 6. Drain Current vs. Case
Temperature**

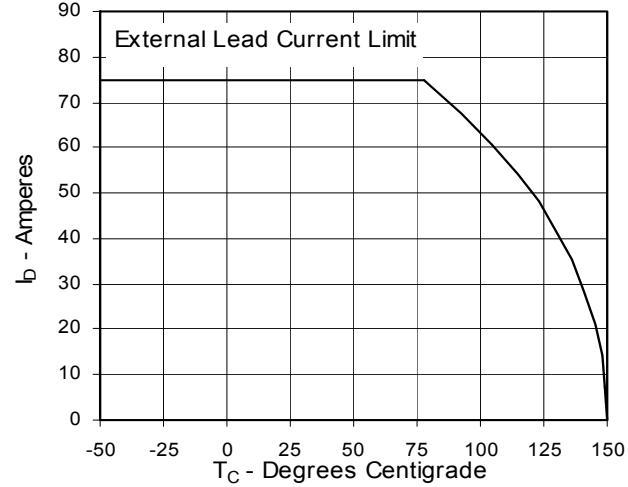


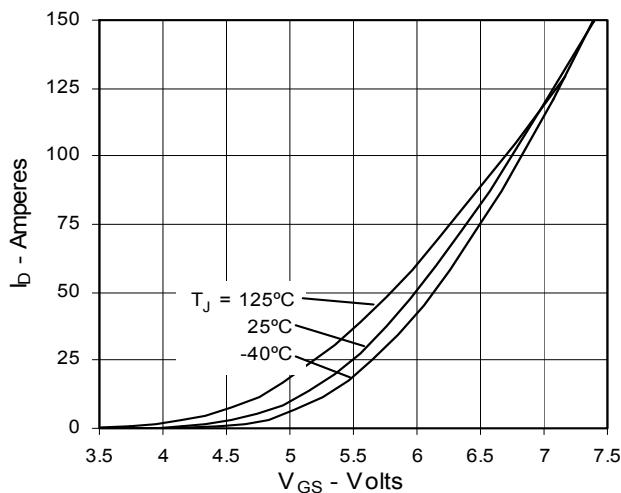
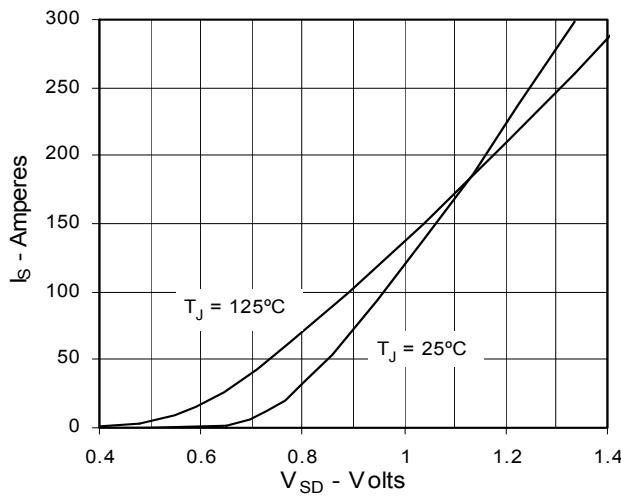
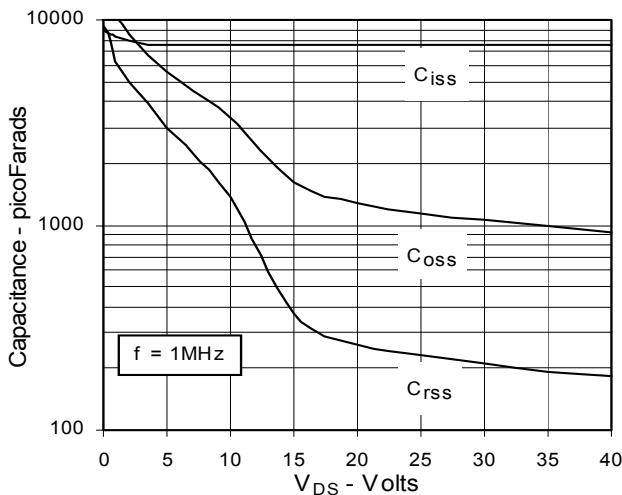
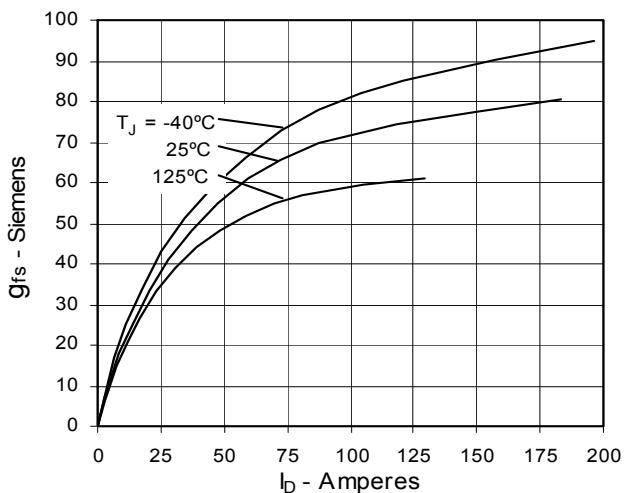
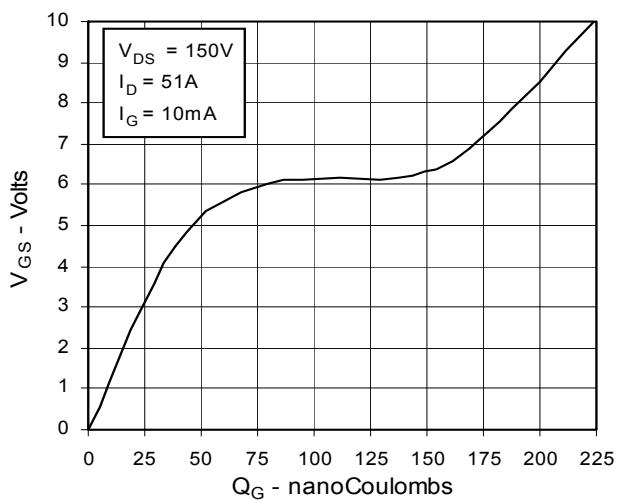
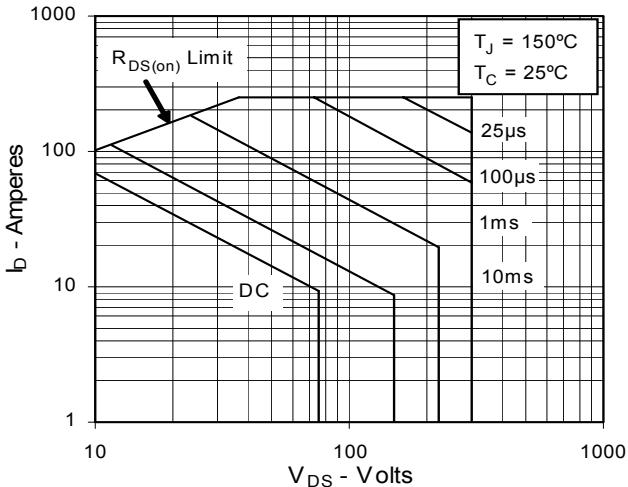
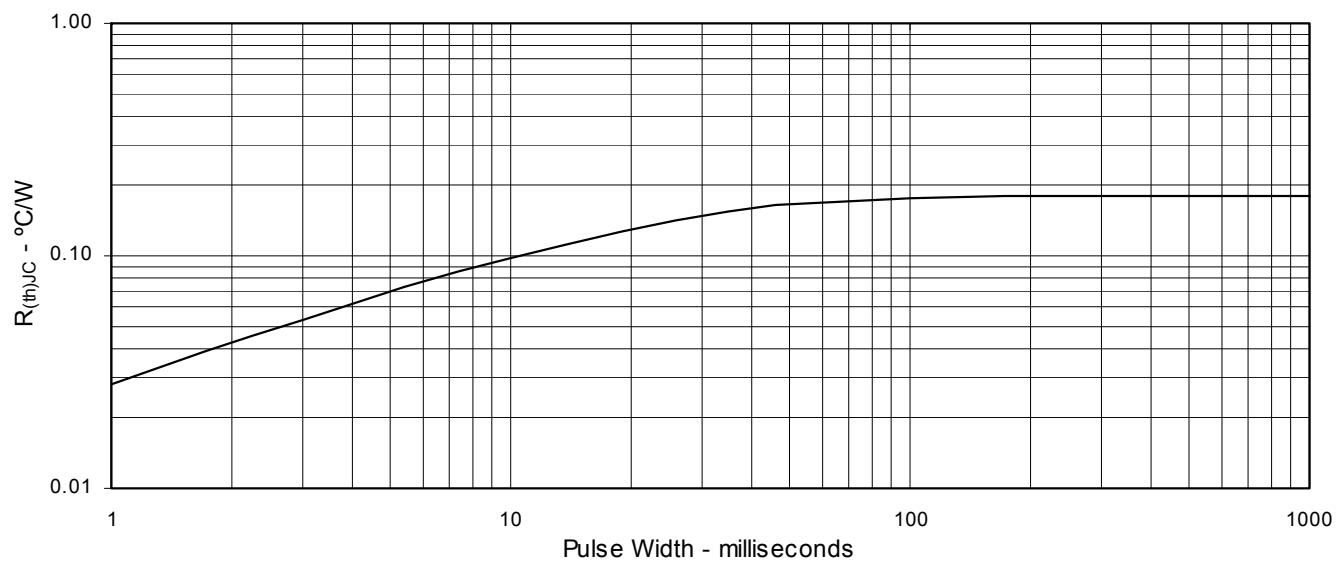
Fig. 7. Input Admittance**Fig. 9. Source Current vs. Source-To-Drain Voltage****Fig. 11. Capacitance****Fig. 8. Transconductance****Fig. 10. Gate Charge****Fig. 12. Forward-Bias Safe Operating Area**

Fig. 13. Maximum Transient Thermal Resistance



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[DMN1006UCA6-7](#) [DMN16M9UCA6-7](#)